

Abstract

In a non-volatile semiconductor memory device (1) according to the present invention, a capacitive sidewall insulating film (21) of a capacitive element (C1, C2) is made of a layer same as that of a sidewall spacer (13a, 13b) of a memory cell (2), the film qualities and thicknesses of which are adjusted mainly for breakdown voltage. The configuration leads to an improved breakdown voltage characteristic and a stabilized capacitor characteristic of the capacitive element (C1, C2). The non-volatile semiconductor memory device (1) does not need a conventionally needed power supply for achieving low voltage application to a capacitive element, thereby achieving a simplified and downsized configuration accordingly.